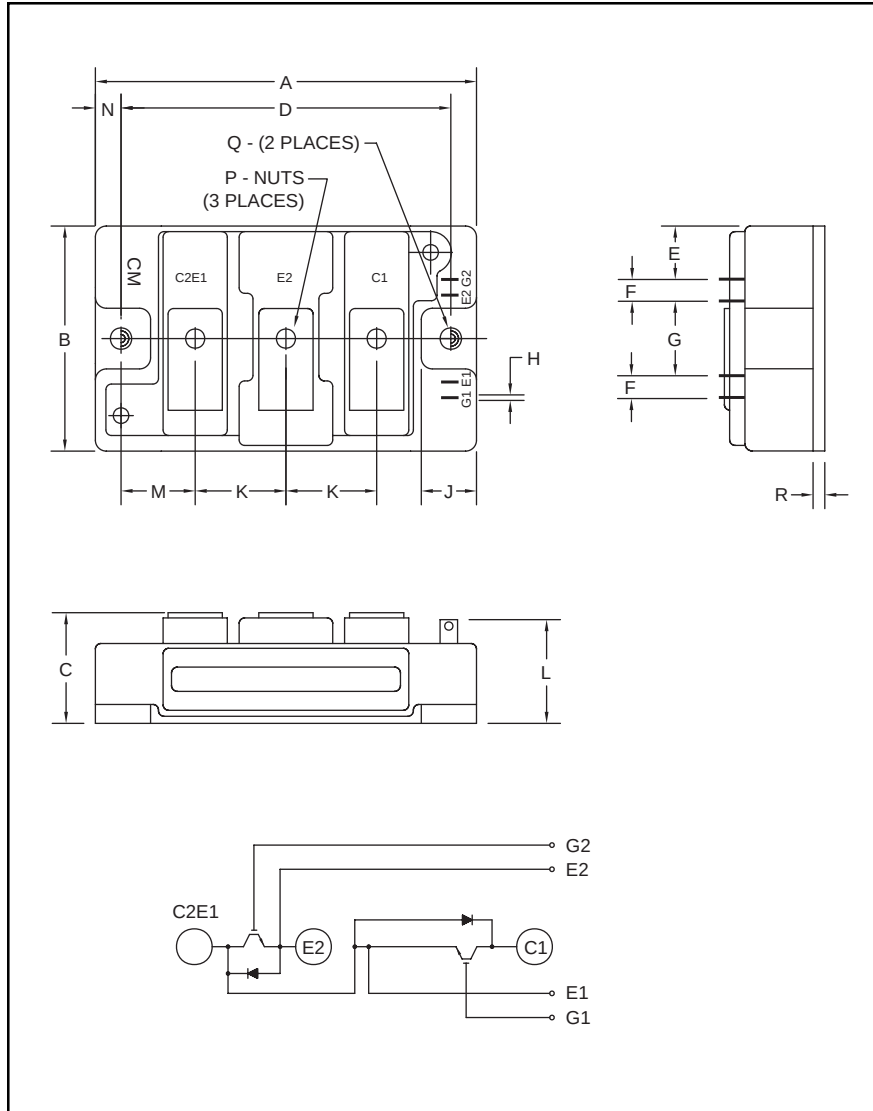


Dual IGBTMOD™ U-Series Module 100 Amperes/1200 Volts



Outline Drawing and Circuit Diagram

Dimensions	Inches	Millimeters
A	3.7	94.0
B	1.89	48.0
C	1.18 +0.04/-0.02	30.0 +1.0/-0.5
D	3.15±0.01	80.0±0.25
E	0.43	11.0
F	0.16	4.0
G	0.71	18.0
H	0.02	0.5

Dimensions	Inches	Millimeters
J	0.53	13.5
K	0.91	23.0
L	1.13	28.7
M	0.67	17.0
N	0.28	7.0
P	M5	M5
Q	0.26 Dia.	6.5 Dia.
R	0.02	4.0



Description:

Powerex IGBTMOD™ Modules are designed for use in switching applications. Each module consists of two IGBT Transistors in a half-bridge configuration with each transistor having a reverse-connected super-fast recovery free-wheel diode. All components and interconnects are isolated from the heat sinking baseplate, offering simplified system assembly and thermal management.

Features:

- ☐ Low Drive Power
- ☐ Low $V_{CE(sat)}$
- ☐ Discrete Super-Fast Recovery Free-Wheel Diode
- ☐ Isolated Baseplate for Easy Heat Sinking

Applications:

- ☐ AC Motor Control
- ☐ Motion/Servo Control
- ☐ UPS
- ☐ Welding Power Supplies
- ☐ Laser Power Supplies

Ordering Information:

Example: Select the complete module number you desire from the table - i.e. CM100DU-24H is a 1200V (V_{CES}), 100 Ampere Dual IGBTMOD™ Power Module.

Type	Current Rating Amperes	V_{CEs} Volts (x 50)
CM	100	24

CM100DU-24H
Dual IGBTMOD™ U-Series Module
 100 Amperes/1200 Volts

Absolute Maximum Ratings, $T_j = 25^\circ\text{C}$ unless otherwise specified

Ratings	Symbol	CM100DU-24H	Units
Junction Temperature	T_j	-40 to 150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-40 to 125	$^\circ\text{C}$
Collector-Emitter Voltage (G-E SHORT)	V_{CES}	1200	Volts
Gate-Emitter Voltage (C-E SHORT)	V_{GES}	± 20	Volts
Collector Current ($T_c = 25^\circ\text{C}$)	I_C	100	Amperes
Peak Collector Current	I_{CM}	200*	Amperes
Emitter Current** ($T_c = 25^\circ\text{C}$)	I_E	100	Amperes
Peak Emitter Current**	I_{EM}	200*	Amperes
Maximum Collector Dissipation ($T_c = 25^\circ\text{C}$, $T_j \leq 150^\circ\text{C}$)	P_C	600	Watts
Mounting Torque, M5 Main Terminal	—	31	in-lb
Mounting Torque, M6 Mounting	—	40	in-lb
Weight	—	310	Grams
Isolation Voltage (Main Terminal to Baseplate, AC 1 min.)	V_{ISO}	2500	Volts

* Pulse width and repetition rate should be such that the device junction temperature (T_j) does not exceed $T_{j(max)}$ rating.

**Represents characteristics of the anti-parallel, emitter-to-collector free-wheel diode (FWDi).

Static Electrical Characteristics, $T_j = 25^\circ\text{C}$ unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Collector-Cutoff Current	I_{CES}	$V_{CE} = V_{CES}$, $V_{GE} = 0V$	—	—	1	mA
Gate Leakage Voltage	I_{GES}	$V_{GE} = V_{GES}$, $V_{CE} = 0V$	—	—	0.5	μA
Gate-Emitter Threshold Voltage	$V_{GE(th)}$	$I_C = 10\text{mA}$, $V_{CE} = 10V$	4.5	6	7.5	Volts
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 100A$, $V_{GE} = 15V$, $T_j = 25^\circ\text{C}$	—	2.9	3.7	Volts
		$I_C = 100A$, $V_{GE} = 15V$, $T_j = 125^\circ\text{C}$	—	2.85	—	Volts
Total Gate Charge	Q_G	$V_{CC} = 600V$, $I_C = 100A$, $V_{GE} = 15V$	—	375	—	nC
Emitter-Collector Voltage**	V_{EC}	$I_E = 100A$, $V_{GE} = 0V$	—	—	3.2	Volts

**Represents characteristics of the anti-parallel, emitter-to-collector free-wheel diode (FWDi).

Dynamic Electrical Characteristics, $T_j = 25^\circ\text{C}$ unless otherwise specified

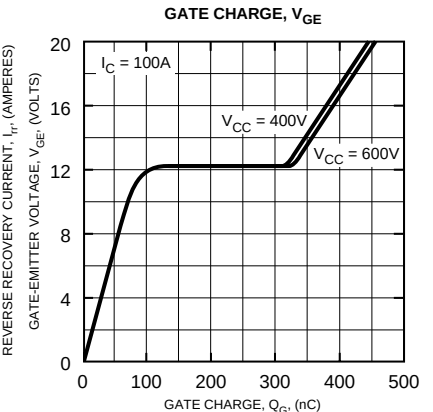
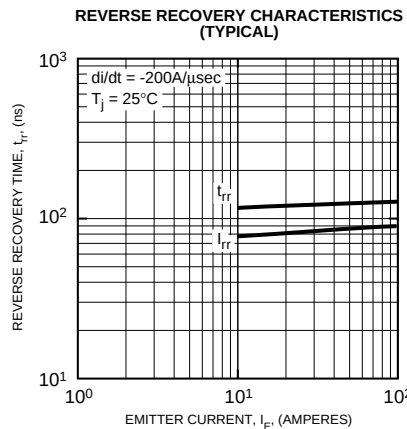
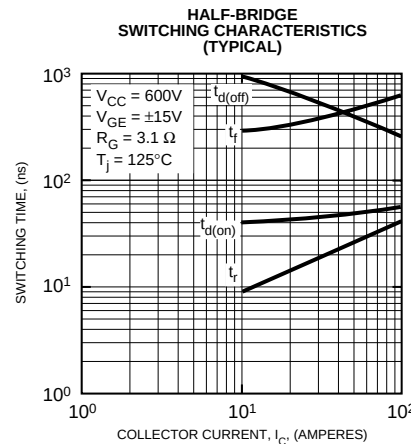
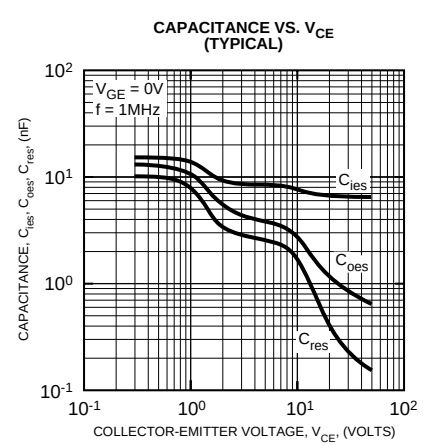
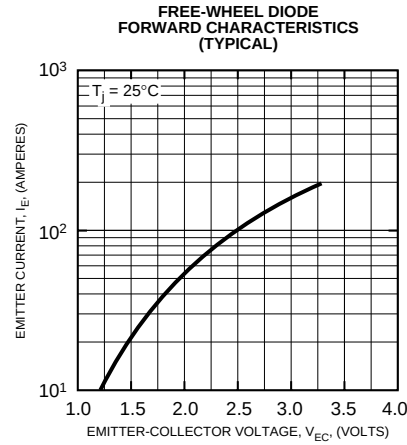
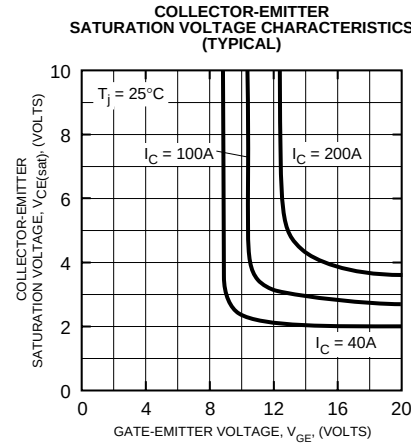
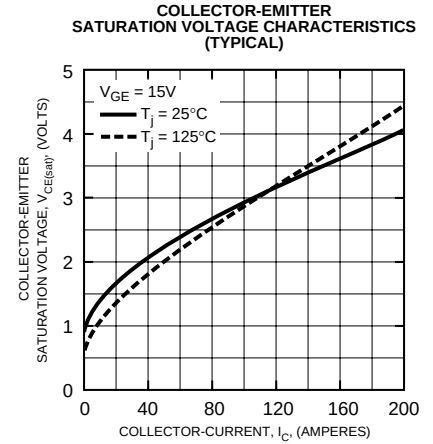
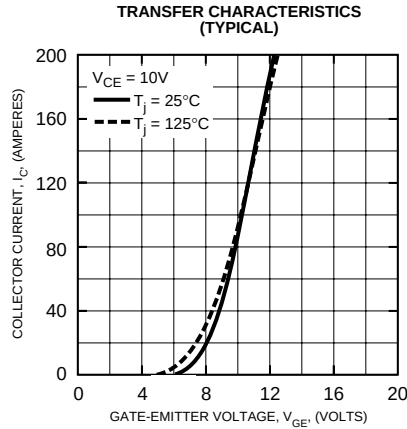
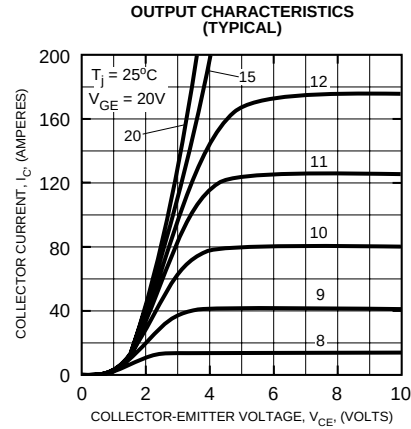
Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Input Capacitance	C_{ies}	$V_{CE} = 10V$, $V_{GE} = 0V$	—	—	15	nf
Output Capacitance	C_{oes}		—	—	5	nf
Reverse Transfer Capacitance	C_{res}		—	—	3	nf
Resistive	Turn-on Delay Time	$V_{CC} = 600V$, $I_C = 100A$,	—	—	100	ns
Load	Rise Time					
Switch	Turn-off Delay Time	$R_G = 3.1\Omega$, Resistive	—	—	300	ns
Times	Fall Time					
Diode Reverse Recovery Time**	t_{rr}	$I_E = 100A$, $di_E/dt = -200A/\mu s$	—	—	300	ns
Diode Reverse Recovery Charge**	Q_{rr}	$I_E = 100A$, $di_E/dt = -200A/\mu s$	—	0.55	—	μC

**Represents characteristics of the anti-parallel, emitter-to-collector free-wheel diode (FWDi).

Thermal and Mechanical Characteristics, $T_j = 25^\circ\text{C}$ unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal Resistance, Junction to Case	$R_{th(j-c)Q}$	Per IGBT 1/2 Module	—	—	0.19	$^\circ\text{C/W}$
Thermal Resistance, Junction to Case	$R_{th(j-c)D}$	Per FWDi 1/2 Module	—	—	0.35	$^\circ\text{C/W}$
Contact Thermal Resistance	$R_{th(c-f)}$	Per Module, Thermal Grease Applied	—	0.035	—	$^\circ\text{C/W}$

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